



TO-92 Plastic-Encapsulate Transistors

A92 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

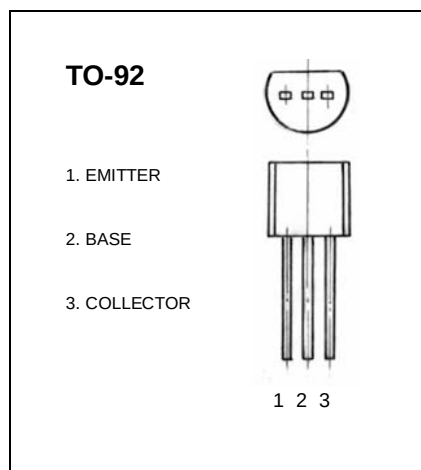
$$I_{CM}: -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -300 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -200 \text{ V}, I_E = 0$			-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$	60			
	$h_{FE(2)}$	$V_{CE} = -10 \text{ V}, I_C = -10 \text{ mA}$	80		250	
	$h_{FE(3)}$	$V_{CE} = -10 \text{ V}, I_C = -80 \text{ mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$			-0.9	V
Transition frequency	f_T	$V_{CE} = -20 \text{ V}, I_C = -10 \text{ mA}$ $f = 30 \text{ MHz}$	50			MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250